



AOD405

P-Channel Enhancement Mode Field Effect Transistor

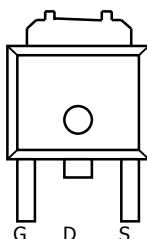
General Description

The AOD405 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and low gate resistance. With the excellent thermal resistance of the DPAK package, this device is well suited for high current load applications.

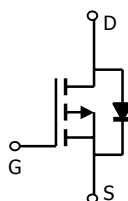
Features

- V_{DS} (V) = -30V
- I_D = -18A
- $R_{DS(ON)} < 32m\Omega$ ($V_{GS} = 20V$)
- $R_{DS(ON)} < 60m\Omega$ ($V_{GS} = 10V$)

TO-252
D-PAK



Top View
Drain Connected to
Tab



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{B,G}	$T_A=25^\circ\text{C}$ ^G	-18	A
	$T_A=100^\circ\text{C}$ ^B	-18	
Pulsed Drain Current	I_{DM}	-40	
Avalanche Current ^C	I_{AR}	-18	A
Repetitive avalanche energy $L=0.1\text{mH}$ ^C	E_{AR}	16	mJ
Power Dissipation ^B	$T_C=25^\circ\text{C}$	60	W
	$T_C=100^\circ\text{C}$	30	
Power Dissipation ^A	$T_A=25^\circ\text{C}$	2.5	W
	$T_A=70^\circ\text{C}$	1.6	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	16.7	25	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	40	50
Maximum Junction-to-Case ^C	$R_{\theta JL}$	1.9	2.5	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-1.2	-2	-2.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}$, $V_{DS}=-5\text{V}$	-40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$, $I_D=-18\text{A}$ $T_J=125^\circ\text{C}$		24.5 36	32 43	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$, $I_D=-10\text{A}$		41	60	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-18\text{A}$		17		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$		-0.76	-1	V
I_S	Maximum Body-Diode Continuous Current				-18	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-15\text{V}$, $f=1\text{MHz}$		920	1100	pF
C_{oss}	Output Capacitance			190		pF
C_{rss}	Reverse Transfer Capacitance			122		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		3.6	4.5	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge (10V)	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $I_D=-18\text{A}$		18.7	23	nC
$Q_g(4.5\text{V})$	Total Gate Charge (4.5V)			9.7		nC
Q_{gs}	Gate Source Charge			2.54		nC
Q_{gd}	Gate Drain Charge			5.4		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $R_L=0.82\Omega$, $R_{GEN}=3\Omega$		7.8		ns
t_r	Turn-On Rise Time			8.7		ns
$t_{D(off)}$	Turn-Off Delay Time			17.7		ns
t_f	Turn-Off Fall Time			8.5		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-18\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		21.4	26	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-18\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		13		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any a given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

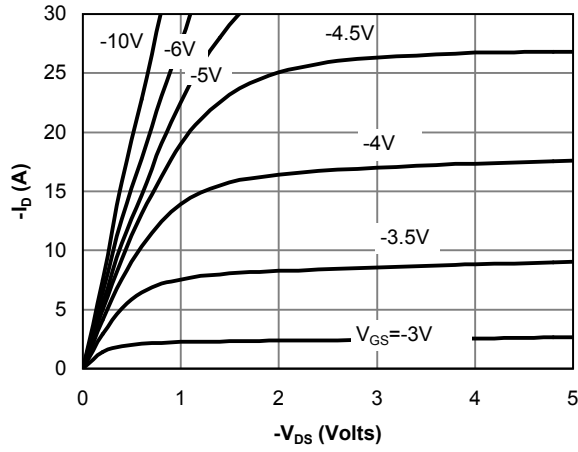


Fig 1: On-Region Characteristics

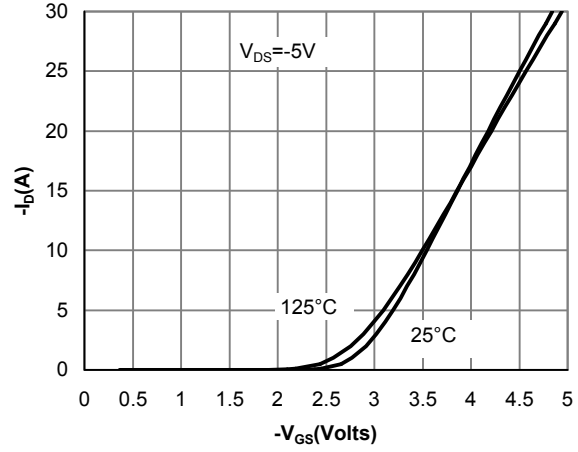


Figure 2: Transfer Characteristics

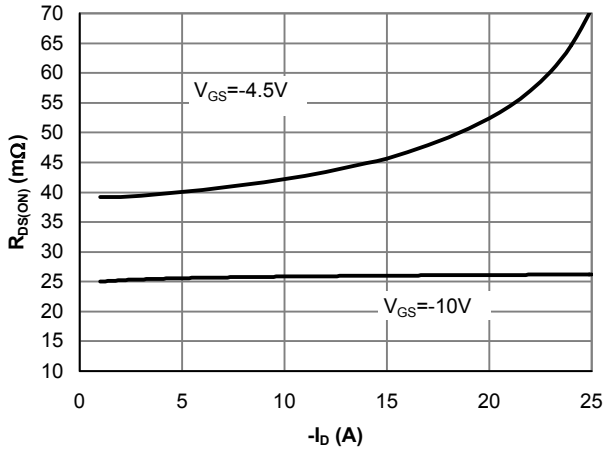


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

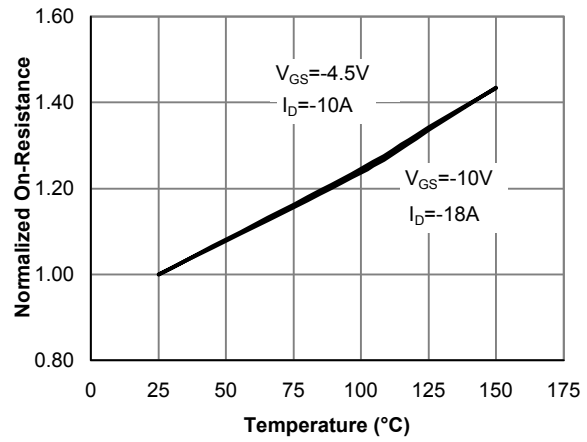


Figure 4: On-Resistance vs. Junction Temperature

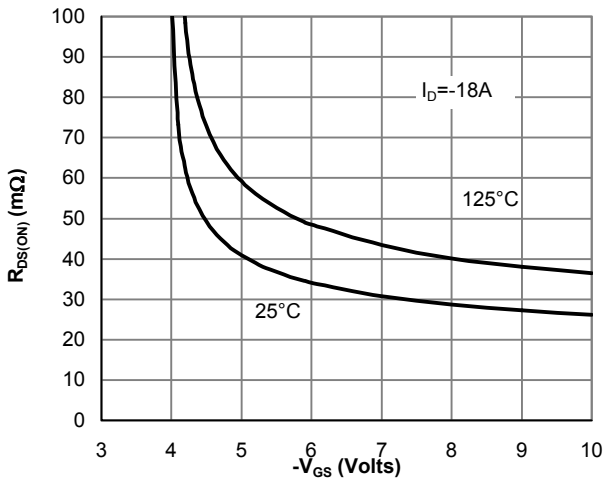


Figure 5: On-Resistance vs. Gate-Source Voltage

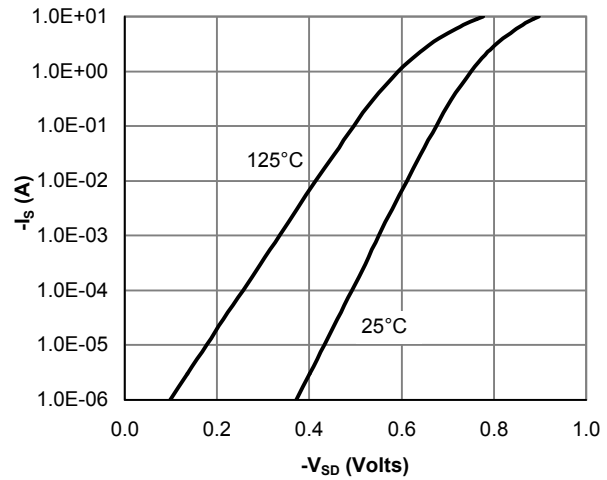


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

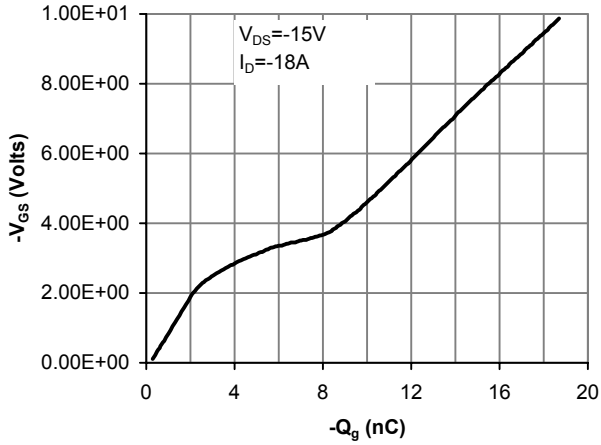


Figure 7: Gate-Charge Characteristics

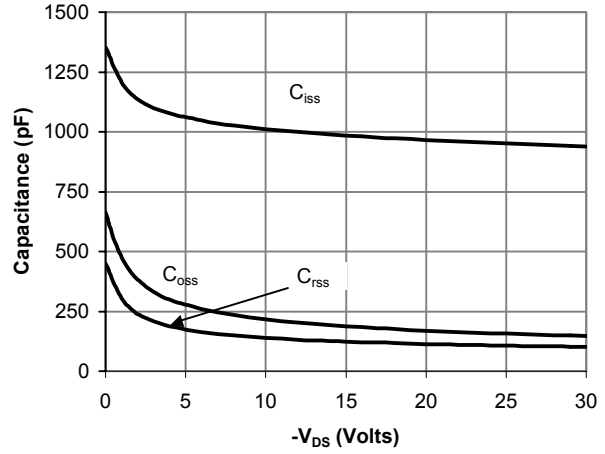


Figure 8: Capacitance Characteristics

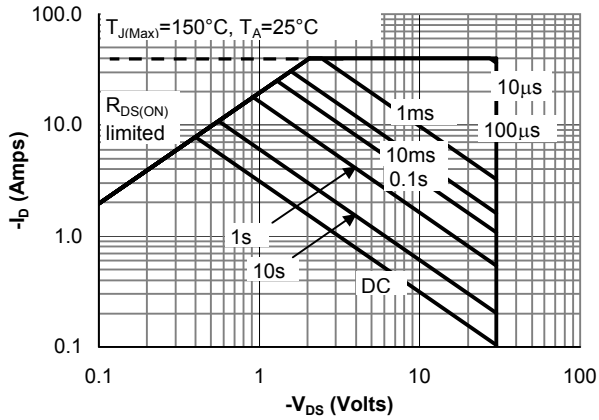


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

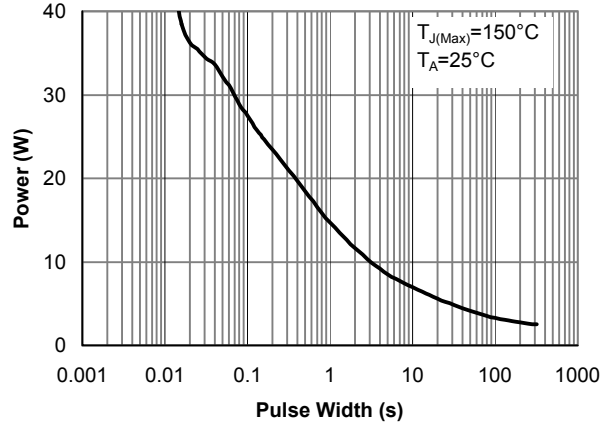


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

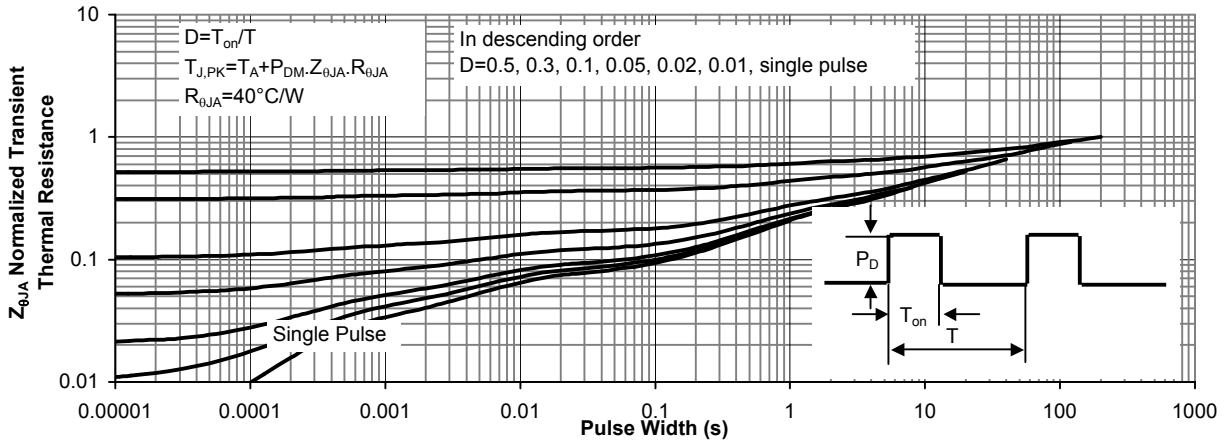


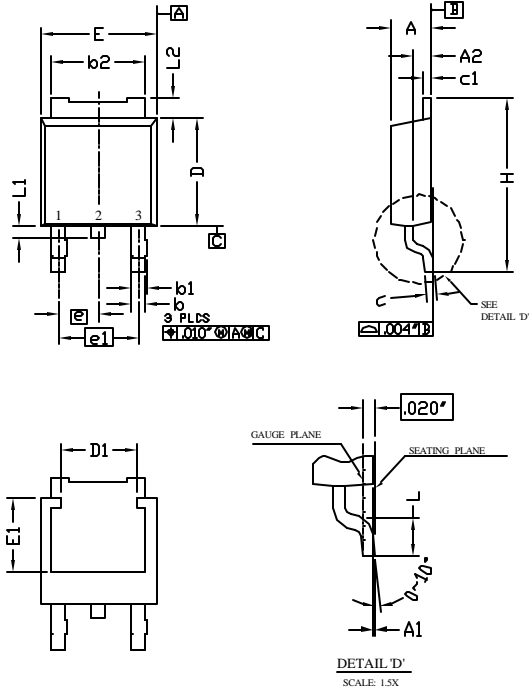
Figure 11: Normalized Maximum Transient Thermal Impedance



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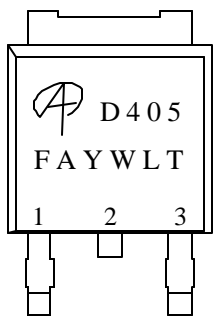
Document No.	PD-00115
Version	rev A
Title	AOD405 Package Data Sheet



	DIMENSION IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	2.235	2.286	2.388	0.088	0.090	0.094
A1	0.000	----	0.102	0.000	----	0.004
A2	0.889	----	1.143	0.035	----	0.045
b	0.686	0.762	0.889	0.027	0.030	0.035
b1	0.889	----	1.143	0.035	----	0.045
b2	5.207	4.45	5.461	0.205	----	0.215
c	0.457	0.508	0.559	0.018	0.020	0.022
c1	0.483	----	0.584	0.019	----	0.023
D	5.969	6.096	6.223	0.235	0.240	0.245
D1	4.318	----	5.334	0.170	----	0.210
E	6.477	6.604	6.731	0.255	0.260	0.265
E1	4.318	----	----	0.170	----	----
e	2.286 BSC.			0.090 BSC.		
e1	4.572 BSC.			0.180 BSC.		
H	9.779	----	10.414	0.385	----	0.410
L	1.270	----	2.032	0.050	----	0.080
L1	0.635	----	1.016	0.025	----	0.040
L2	0.889	----	1.270	0.035	----	0.050

- NOTE
1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS
 2. DIMENSION L IS MEASURED IN GAGE PLANE
 3. TOLERANCE 0.10 mm UNLESS OTHERWISE SPECIFIED
 4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
 5. FOLLOWED FROM JEDEC TO-252 (AA)

PACKAGE MARKING DESCRIPTION

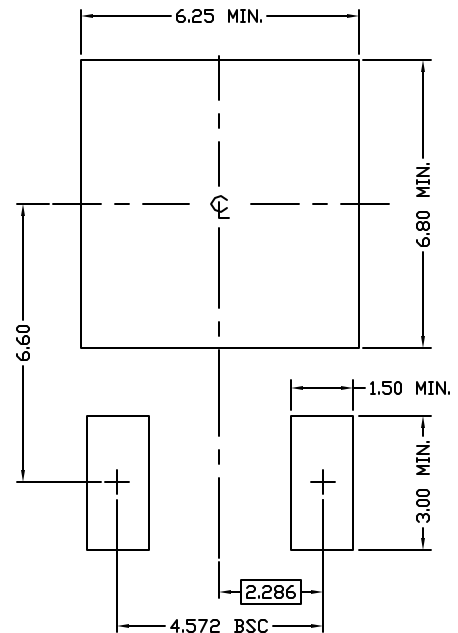


- NOTE:
- AOS LOGO
 - D405 - PART NUMBER CODE.
 - F&A - FOUNDRY AND ASSEMBLY LOCATION
 - Y - YEAR CODE
 - W - WEEK CODE.
 - L T - ASSEMBLY LOT CODE

DPAK PART NO. CODE

PART NO.	CODE
AOD405	D405

RECOMMENDED LAND PATTERN



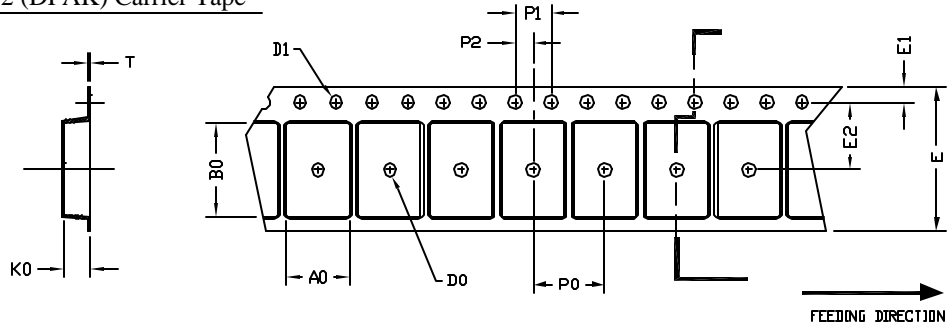
UNIT: mm



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TO-252 (DPAK)
Tape and Reel Data

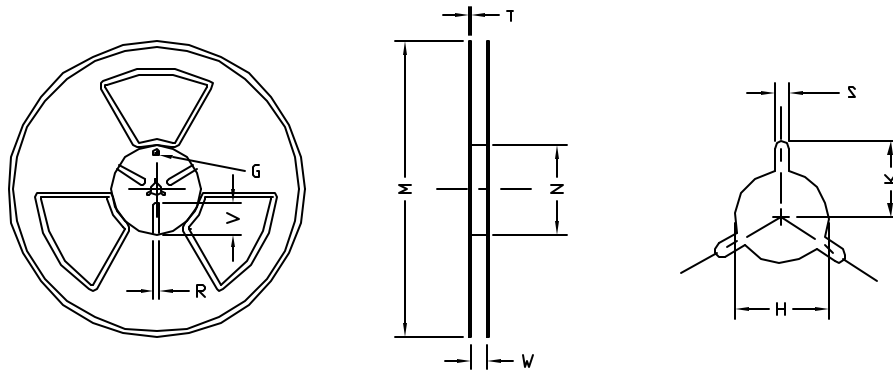
TO-252 (DPAK) Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252(DPAK) (16 mm)	6.90 ±0.10	10.50 ±0.10	2.70 ±0.10	1.50 ±0.10	1.50 MIN.	16.00 ±0.10	1.75 ±0.10	7.50 ±0.10	8.00 ±0.10	4.00 ±0.10	2.00 ±0.10	0.30 ±0.05

TO-252 (DPAK) Reel



UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ330	φ330.00 ±0.10	φ99.50 ±0.10	17.50 ±0.50	2.30	φ13.50 ±0.10	10.60	2.50 ±0.10	---	---	---

TO-252 (DPAK)

Leader / Trailer
& Orientation

